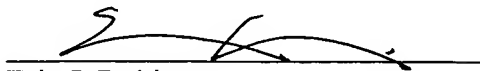


REMARKS

Claim 5 has been amended to correct the multiple dependencies therein.

Examination on the merits is requested.

Respectfully submitted,

  
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VERSION WITH MARKINGS TO SHOW CHANGES MADE

5. (Amended) The bipolar transistor according to any one of claims 1 through [4] 3, wherein:

said substrate is a silicon substrate;

said first semiconductor layer is an Si layer;

said second semiconductor layer is an SiGe layer or an SiGeC layer;

and

said third semiconductor layer is an Si layer.

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